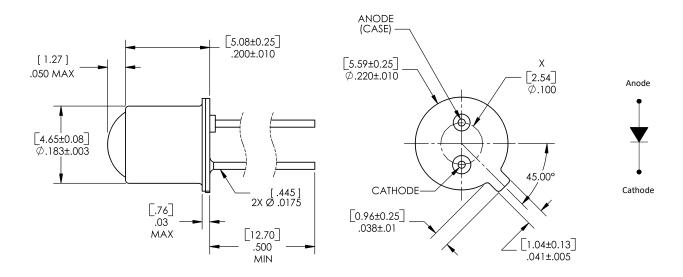
Hermetic Infrared Diode

OP130 Series



Electrical Specifications

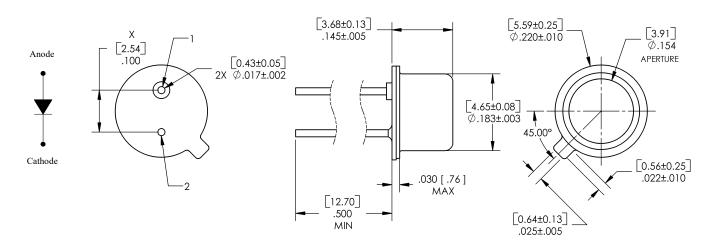
OP130, OP131, OP132, OP133



X THIS DIMENSION CONTROLLED AT HOUSING SURFACE.

DIMENSIONS ARE IN: [MILLIMETERS] INCHES

OP130W and OP133W



 ${\sf X}\,$ THIS DIMENSION CONTROLLED AT HOUSING SURFACE.

DIMENSIONS ARE IN: [MILLIMETERS] INCHES

Pin#	LED			
1	Anode			
2	Cathode			

General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

TT Electronics | OPTEK Technology 2900 E. Plano Pkwy, Plano, TX 75074 | Ph: +1 972 323 2200 www.ttelectronics.com | sensors@ttelectronics.com

© TT electronics plc lssue D 04/2019 Page 2

Hermetic Infrared Diode

OP130 Series



Electrical Specifications

osolute Maximum Ratings (T _A = 25° C unless otherwise noted)				
Storage Temperature Range	-65° C to +150° C			
Operating Temperature Range	-65° C to +125° C			
Reverse Voltage	2.0 V			
Continuous Forward Current	100 mA			
Peak Forward Current (2 us pulse width, 0.1% duty cycle)	10.0 A			
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽¹⁾⁽²			
Power Dissipation	200 mW ⁽³			

Electrical Characteristics (T _A = 25° C unless otherwise noted)							
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
P _O	Radiant Power Output						
	OP130, OP130W	1.0	-	-	mW		
	OP131	3.0	-	-		I _F = 100 mA ^(3)	
	OP132	4.0	-	-			
	OP133, OP133W	5.0	-	-			
V_{F}	Forward Voltage	-	-	1.75	V	I _F = 100 mA ⁽³⁾	
I _R	Reverse Current	-	-	100	μΑ	V _R = 2.0 V	
λ_{P}	Wavelength at Peak Emission	-	935	-	nm	I _F = 10 mA	
β	Spectral Bandwidth between Half Power Points	-	50	-	nm	I _F = 10 mA	

Notes

- 1. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- 2. Derate linearly 2.0 mW/° C above 25° C.
- 3. Measurement made with 100 μ s pulse measured at the trailing edge of the pulse with a duty cycle of 0.1% and an I_F = 100 mA.

Electrical Characteristics (T _A = 25° C unless otherwise noted—for reference only)								
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS		
$\Delta \lambda_P/\Delta T$	Spectral Shift with Temperature	-	+0.30	-	nm/°C	I _F = Constant		
θ_{HP}	Emission Angle at Half Power Points OP130 series OP130W series	-	18 50	-	Degree	I _F = 100 mA		
t _r	Output Rise Time	-	1000	-	ns	I _{F(PK)} =100 mA, PW=10 μs, and D.C.=10.0%		
t _f	Output Fall Time	-	500	-	ns			

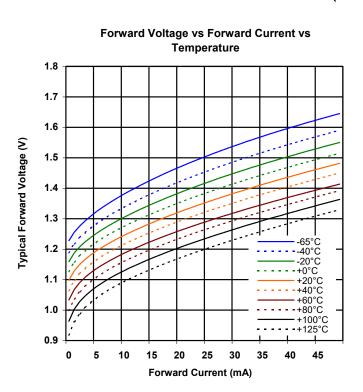
Hermetic Infrared Diode

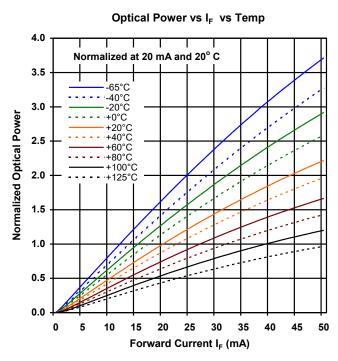
OP130 Series



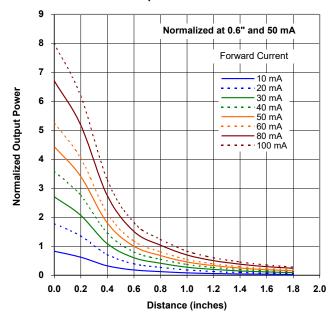
Performance

OP130 Series (including "W" devices)





Distance vs Output Power vs Forward Current



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

TT Electronics | OPTEK Technology 2900 E. Plano Pkwy, Plano, TX 75074 | Ph: +1 972 323 2200 www.ttelectronics.com | sensors@ttelectronics.com

© TT electronics plc Issue D 04/2019 Page 4